# onsemi

# Single Non-Inverting Buffer with Open Drain Output

# NLV74VHC1G07, NLV74VHC1GT07

The NLV74VHC1G07 / NLV74VHC1GT07 is a single non-inverting buffer with open drain output in tiny footprint packages. The NLV74VHC1G07 has CMOS-level input thresholds while the NLV74VHC1GT07 has TTL-level input thresholds.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when  $V_{CC} = 0$  V and when the output voltage exceeds  $V_{CC}$ . These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

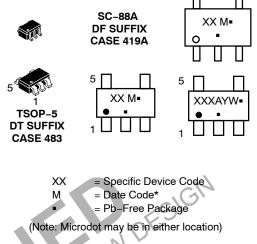
# Features

- $\bullet\,$  Designed for 2.0 V to 5.5 V V\_{CC} Operation
- 3.5 ns t<sub>PD</sub> at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- I<sub>OFF</sub> Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A and TSOP-5 Packages
- Chip Complexity < 100 FETs

THISDE

- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Figure 1. Logic Symbol



# ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 7 of this data sheet.

# MARKING DIAGRAMS

# NLV74VHC1G07, NLV74VHC1GT07

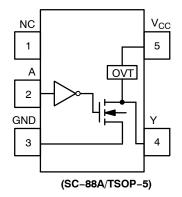
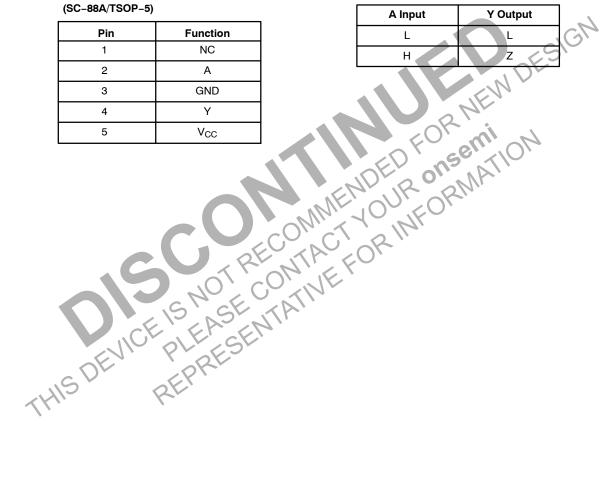


Figure 2. Pinout (Top View)

**FUNCTION TABLE** 

PIN ASSIGNMENT



#### CONFIDENTIAL AND PROPRIETARY NLV74VHC1G07, NLV74VHC1GT07 NOT FOR PUBLIC RELEASE

## **MAXIMUM RATINGS**

Symbol	C	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V	
V <sub>IN</sub>	DC Input Voltage	-0.5 to +7.0	V	
V <sub>OUT</sub>	DC Output Voltage	1Gxx	–0.5 to V <sub>CC</sub> + 0.5	V
		1GTxx Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	$\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } +7.0 \\ -0.5 \text{ to } +7.0 \end{array}$	
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	1Gxx V <sub>OUT</sub> > V <sub>CC</sub> , V <sub>OUT</sub> < GND	±20	mA
		1GTxx V <sub>OUT</sub> < GND	-20	
I <sub>OUT</sub>	DC Output Source/Sink Current		±25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC Supply Current per Supply Pir	±50	mA	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Ca	se for 10 secs	260	o∘C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{JA}$	Thermal Resistance (Note 2)	SC-88A TSOP-5	377 320	°C/W
P <sub>D</sub>	Power Dissipation in Still Air	SC-88A TSOP-5	NF 332 390	mW
MSL	Moisture Sensitivity		Level 1	-
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V <sub>ESD</sub>	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I <sub>Latchup</sub>	Latchup Performance (Note 4)	NE OU'C	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Applicable to devices with outputs that may be tri-stated.
 Applicable to devices with outputs that may be tri-stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A. THIS DEVICE PLEASENTAT

4. Tested to EIA/JESD78 Class II.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	C	Min	Max	Unit	
V <sub>CC</sub>	Positive DC Supply Voltage			5.5	V
V <sub>IN</sub>	DC Input Voltage			5.5	V
V <sub>OUT</sub>	DC Output Voltage	1Gxx	0	V <sub>CC</sub>	V
		1GTxx Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	0 0 0	V <sub>CC</sub> 5.5 5.5	
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 3.0 V to 3.6 V V <sub>CC</sub> = 4.5 V to 5.5 V	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS (NLV74VHC1G07)

DC ELECTRICAL CHARACTERISTICS (NLV74VHC1G07)										T	
		Test	Vcc	٦	A = 25°	С	<b>−40°C</b> ≤ 1	Γ <sub>A</sub> ≤ 85°C	–55°C ≤ T	<sub>A</sub> ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Мах	Min	Max	Unit
V <sub>IH</sub>	High-Level Input		2.0	1.5	-	-	1.5	-	1.5	-	V
	Voltage		3.0	2.1	-	-	2.1		2.1	-	
			4.5	3.15	-		3.15	Nr	3.15	-	
			5.5	3.85	+	1	3.85	<u> </u>	3.85	-	
V <sub>IL</sub>	Low-Level Input		2.0	-		0.5		0.5	4	0.5	V
	Voltage		3.0	-	-	0.9	N	0.9	<u>V-</u>	0.9	
			4.5	-	-	1.35	~ ~ O	1.35	-	1.35	
			5.5			1.65	JF.C	1.65	-	1.65	
V <sub>OL</sub>	Low-Level Output	$V_{IN} = V_{IH} \text{ or } V_{IL}$		-	V h.	7	F	/			V
	Voltage	I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 50 μA	2.0 3.0	-O`	0.0 0.0	0.1 0.1	14.	0.1 0.1	-	0.1 0.1	
		$I_{OL} = 50 \ \mu A$	4.5	$\mathcal{O}_{-}$	0.0	0.1		0.1	_	0.1	
		$1_{01} = 4 \text{ mA}$	3.0		Ϋ́_, ·	0.36	-	0.44	-	0.52	
		$I_{OL} = 8 \text{ mA}$	4.5	77	1F	0.36	-	0.44	-	0.52	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	2.0 to 5.5	X	7	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>OZ</sub>	3-State Output Leakage Current	V <sub>OUT</sub> = 0 V to 5.5 V	5.5	<u> </u>	-	±0.25	-	±2.5	-	±2.5	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V	0.0	-	-	1.0	-	10	-	10	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	-	-	1.0	-	20	-	40	μΑ

# DC ELECTRICAL CHARACTERISTICS (NLV74VHC1GT07)

		Test	v <sub>cc</sub>	٦	「 <sub>A</sub> = 25°	C	<b>-40°C</b> ≤ 1	Γ <sub>A</sub> ≤ 85°C	–55°C ≤ T	<sub>A</sub> ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Мах	Min	Мах	Unit
VIH	High-Level Input		2.0	1.0	-		1.0	-	1.0	_	V
	Voltage		3.0	1.4	-		1.4	-	1.4	_	
			4.5	2.0	-		2.0	_	2.0	_	
			5.5	2.0	-		2.0	-	2.0	-	
V <sub>IL</sub>	Low-Level Input		2.0	-	-	0.28	-	0.28	-	0.28	V
	Voltage		3.0	-	-	0.45	-	0.45	-	0.45	
			4.5	-	-	0.8	-	0.8	-	0.8	
			5.5	-	-	0.8	-	0.8	-	0.8	
V <sub>OL</sub>	Low-Level Output Voltage	$ \begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 50 \ \mu A \\ I_{OL} = 50 \ \mu A \\ I_{OL} = 50 \ \mu A \\ I_{OL} = 4 \ m A \\ I_{OL} = 8 \ m A \end{array} $	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 - -	0.1 0.1 0.36 0.36	- - - -	0.1 0.1 0.44 0.44		0.1 0.1 0.52 0.52	V
I <sub>IN</sub>	Input Leakage Cur- rent	V <sub>IN</sub> = 5.5 V or GND	2.0 to 5.5	-	-	±0.1	-	±1.0		±1.0	μA
I <sub>OZ</sub>	3-State Output Leakage Current	V <sub>OUT</sub> = 0 V to 5.5 V	5.5	-	-	±0.25	-	±2.5	$V_{\overline{\lambda}}$	±2.5	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	-	-	1.0		2 10	-	10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5		-	1.0	OF.	S <sup>20</sup>	1014	40	μΑ
I <sub>CCT</sub>	Increase in Quiescent Supply Current per Input Pin	One Input: $V_{IN} = 3.4 V$ ; Other Input at $V_{CC}$ or GND	5.5	-	MF	1.35	URC	1.5 A	-	1.65	mA

# AC ELECTRICAL CHARACTERISTICS

			1 Kr	<u>л</u> у	<sub>A</sub> = 25°	ह	–40°C ≤ <sup>-</sup>	Γ <sub>A</sub> ≤ 85°C	–55°C ≤ T	<sub>A</sub> ≤ 125°C	
Symbol	Parameter	Conditions	V <sub>cc</sub> (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PZL</sub>	Propagation Delay,	C <sub>L</sub> = 15 pF	3.0 to 3.6	N.	5.0	7.1	-	8.5	-	10.0	ns
	A to Y (Figures 3 and 4)	C <sub>L</sub> = 50 pF	SIN	/ - · ·	7.5	10.6	-	12.0	-	14.5	
		C <sub>L</sub> = 15 pF	4.5 to 5.5	-	3.8	5.5	-	6.5	-	8.0	
	EVI	C <sub>L</sub> = 50 pF	E	-	5.3	7.5	-	8.5	-	10.0	
t <sub>PLZ</sub>	Propagation Delay,	C <sub>L</sub> = 15 pF	3.0 to 3.6	-	6.5	9.7	_	11.5	_	12.5	ns
	A to Y (Figures 3 and 4)	C <sub>L</sub> = 50 pF		-	7.5	10.6	_	12.0	_	14.5	1
~	riguroo o ana rj	C <sub>L</sub> = 15 pF	4.5 to 5.5	-	4.8	6.8	_	8.0	_	9.0	1
		C <sub>L</sub> = 50 pF		-	5.3	7.5	_	10.0	_	12.0	1
C <sub>IN</sub>	Input Capacitance			-	4.0	10	_	10	_	10	pF
C <sub>OUT</sub>	Output Capacitance	Output in High Impedance State		-	6.0	-	-	-	_	_	pF

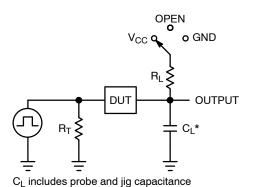
Power Dissipation Capacitance (Note 5) Cp

5.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

8.0

рF

f = 1 MHz

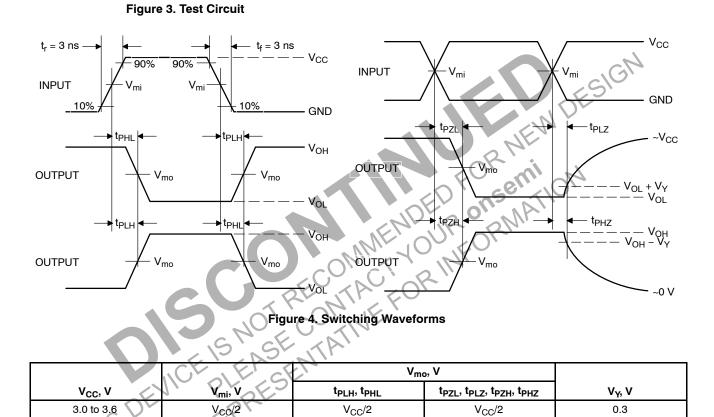


 $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

V<sub>CC</sub>/2

Switch Position	С <sub>L</sub> , pF	$R_L, \Omega$
Open	See AC Characteristics Table	Х
V <sub>CC</sub>		1 k
GND		1 k
	Position Open V <sub>CC</sub>	Position         See AC Characteristics Table           V <sub>CC</sub>

X = Don't Care



 $V_{CC}/2$ 

 $V_{CC}/2$ 

0.3

4.5	to	5.5

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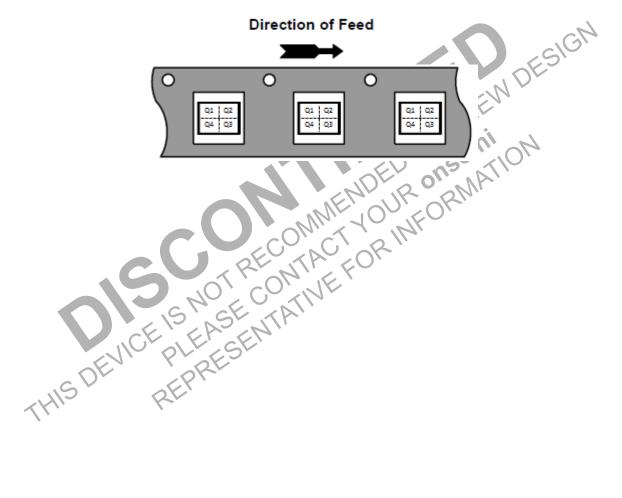
## **ORDERING INFORMATION**

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping <sup>†</sup>
MC74VHC1G07DFT1G-L22038	SC-88A	V7	Q2	3000 / Tape & Reel
NLVVHC1G07DFT1G*	SC-88A	V7	Q2	3000 / Tape & Reel
NLVVHC1G07DFT2G*	SC-88A	V7	Q4	3000 / Tape & Reel
MC74VHC1G07DTT1G	TSOP-5	V7	Q4	3000 / Tape & Reel
NLV74VHC1G07DTT1G*	TSOP-5	V7	Q4	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

# **PIN 1 ORIENTATION IN TAPE AND REEL**



# **NSEM**



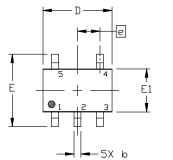
## SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE M**

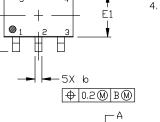
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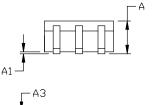
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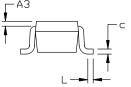
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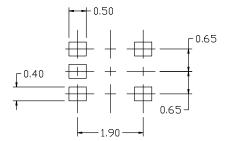
DATE 11 APR 2023











#### RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS					
MIU	MIN.	NDM.	MAX.			
A	0.80	0.95	1.10			
A1			0.10			
A3	0.20 REF					
b	0.10	0.20	0.30			
С	⊂ 0.10		0.25			
D	1.80	2.00	5'50			
E	E 2.00		5'50			
E1	E1 1.15		1,35			
e		0.65 BSI	С			
L	0.10	0.15	0.30			

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,

PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,

OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

CONTROLLING DIMENSION: MILLIMETERS 419A-01 DBSOLETE, NEW STANDARD 419A-02

# **GENERIC MARKING**





\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

Μ = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	E
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called efer to the device
DOCUMENT NUMBER:	98ASB42984B			ot when accessed directly from when stamped "CONTROLLED (	
DESCRIPTION:	SC-88A (SC-70-	PAGE 1 OF 1			

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## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

#### TSOP-5 3.00x1.50x0.95, 0.95P **CASE 483** ISSUE P DATE 01 APR 2024 NOTES: 5X b 0.20 C A B DIMENSIONING AND TOLERANCING CONFORM TO ASME NOTE 5 1. Y14.5-2018. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. 2. В 3. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. Ė1 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D. 5 OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS PIN 1 ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND IDENTIFIER MORE THAN 0.2 FROM BODY. le A MILLIMETERS DIM NOM. TOP VIEW MIN. MAX 0.900 1.000 1.100 DETAIL A А (A2) A1 0.010 0.055 0.100 Α2 0.950 REF 0.250 0.375 0.500 h 0.100 0.180 0.260 с 0.05 C SEATING 2.850 D 3.000 3.150 Ċ A1 PLANE END VIEW SIDE VIEW Ε 2.500 2.750 3.000 1.350 E1 1.500 1.650 0.950 BSC е 0.250 GAUGE 0.400 L 0.200 0.600 0° 5° 10° Θ 1.900Ð 0.950 "A DETAIL SCALE 2:1 GENERIC **MARKING DIAGRAM\*** 2.400 5 5 XXXAYW= XXX M= 1.000 1 0.700Analog Discrete/Logic RECOMMENDED MOUNTING FOOTPRINT\* XXX = Specific Device Code XXX = Specific Device Code FOR ADDITIONAL INFORMATION ON OUR Pb-FREE А = Assembly Location Μ = Date Code STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD = Pb-Free Package v = Year THE ON SEMICONDUCTOR SOLDERING AND MOUNTING W = Work Week TECHNIQUES REFERENCE MANUAL, SOLDERRM/D. = Pb-Free Package (Note: Microdot may be in either location) \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. DOCUMENT NUMBER: 98ARB18753C Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** TSOP-5 3.00x1.50x0.95, 0.95P PAGE 1 OF 1 onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

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